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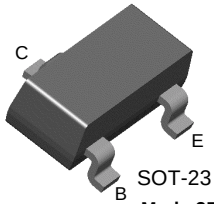
MMBTH10RG

NPN RF Transistor

- This device is designed for use in low noise UHF/VHF amplifiers, with collector currents in the 100 μA to 20 mA range in common emitter or common base mode of operations, and in low frequency drift, high output UHF oscillators.
- Sourced from process 42.



SOT-23
Mark: 3E

1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current - Continuous	50	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These rating are based on a maximum junction temperature of 150 degrees C.
2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

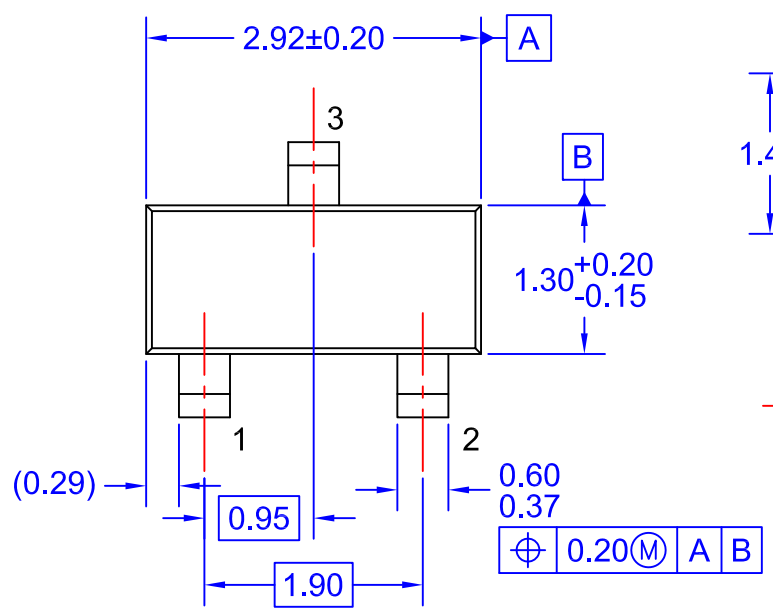
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage *	I_C = 1.0 mA, I_B = 0	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 μA, I_E = 0	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 1.0 μA, I_C = 0	4.0		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 30 V, I_E = 0		100	nA
On Characteristics					
h_{FE}	DC Current Gain	I_C = 1.0 mA, V_{CE} = 6.0 V	50	120	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 5.0 mA		0.2	V
Small Signal Characteristics					
f_T	Current Gain - Bandwidth Product	I_C = 2.0 mA, V_{CE} = 10 V, f = 100 MHz	450		MHz
C_{cb}	Collector-Base Capacitance	V_{CB} = 10 V, I_E = 0, f = 1.0 MHz		0.6	pF
rb'Cc	Collector Base Time Constant	I_C = 5.0 mA, V_{CB} = 10 V, f = 79.8 MHz		12	pS

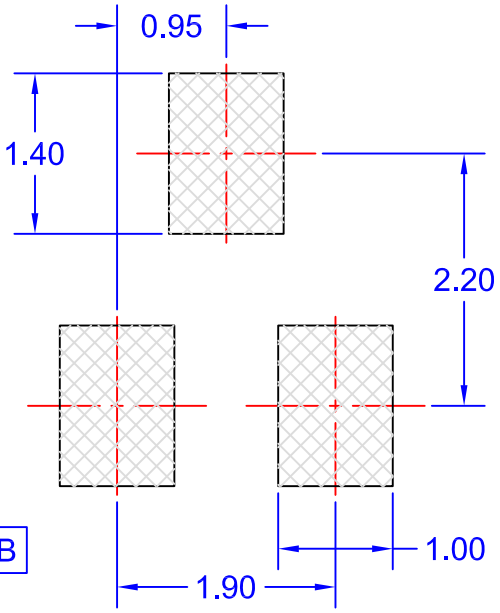
* Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Thermal Characteristics T_a=25°C unless otherwise noted

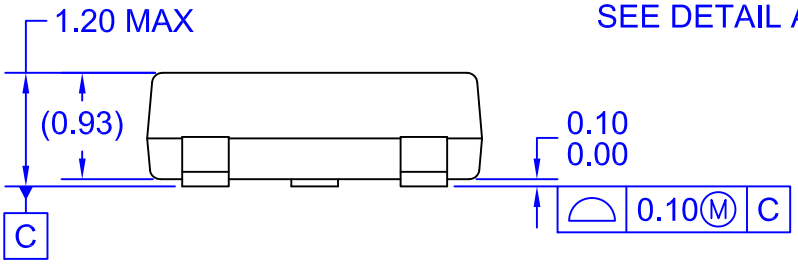
Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation Derate above 25°C	225 1.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	°C/W

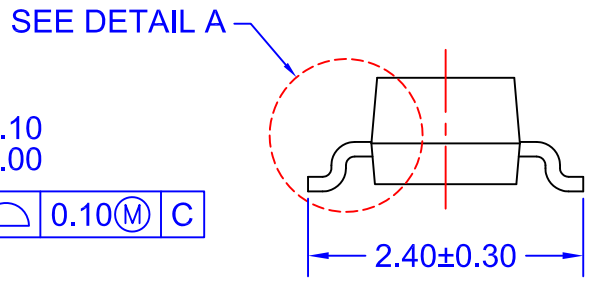
*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

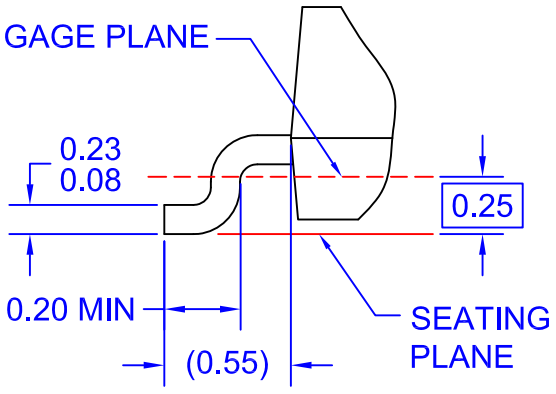




LAND PATTERN
RECOMMENDATION







DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
E) DRAWING FILE NAME: MA03DREV12

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